

Electronic Supplementary Material (ESI) for Nanoscale.  
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## Supporting information

### Transient and Flexible Polymer Memristors Utilizing Full-Solution

#### Processed Polymer Nanocomposites

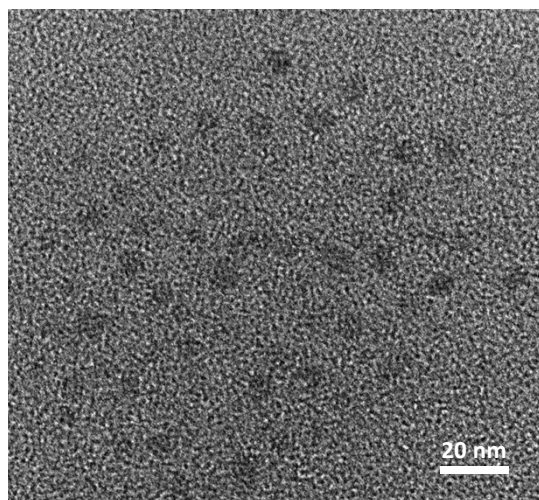
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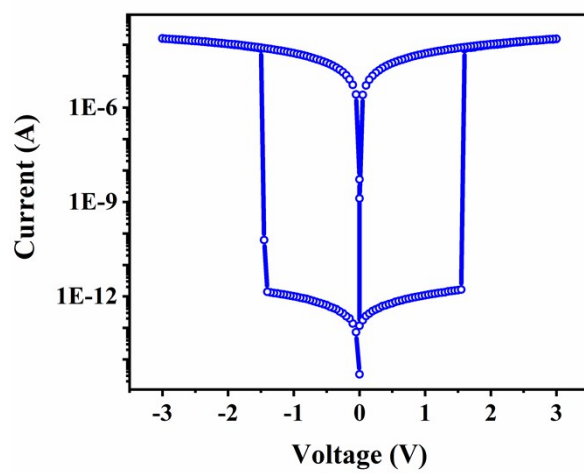
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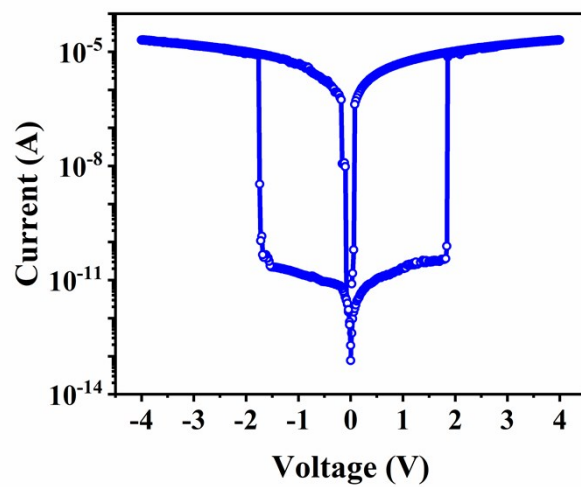
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**Figure S1.** Transmission electron microscopy (TEM) image of synthesized spherical CA QDs.



**Figure S2.** Current versus voltage (I-V) curves of memristor with an architecture of AgNW/AgNP-PVP/AgNW.



**Figure S3.** Current versus voltage (I-V) curves of memristor with an architecture of ITO/CA QD-PVP/Au.